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(54) **MAGNETIC MEMORY DEVICE AND
METHOD FOR FORMING THE SAME**

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ABSTRACT

A magnetic memory device includes a bottom electrode layer, a magnetic tunneling junction (MTJ) stack disposed on the bottom electrode layer, a dielectric cap layer disposed on the MTJ stack, and a metal cap layer disposed on the dielectric cap layer, wherein the metal cap layer comprises a plurality of first metal layers and second metal layers alternately stacked on the dielectric cap layer.

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	<u>14</u>	<u>12</u>	<u>14</u>	
<u>10</u>				